

## 30V 100mA Schottky Diode – SiS30SA1L

Small-signal ultra-low leakage schottky diode in bare die form

Rev 1.0 01/10/20

#### Features:

- Ultra-low leakage current
- Low forward voltage
- 30V breakdown voltage
- Guard-ring for over-voltage protection
- High reliability tested grades & matched characteristic options.

### **Ordering Information**

The following part suffixes apply:

- No suffix MIL-STD-750 /2073 Visual Inspection
- "H" MIL-STD-750 /2073 Visual Inspection+ MIL-PRF-38534 Class H LAT
- "K" MIL-STD-750 /2073 Visual Inspection+ MIL-PRF-38534 Class K LAT

LAT = Lot Acceptance Test.

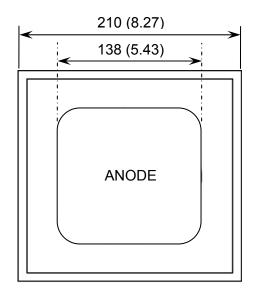
For further information on LAT process flows see below.

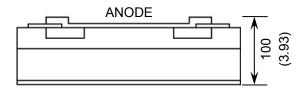
www.siliconsupplies.com\quality\bare-die-lot-qualification

### **Supply Formats:**

- Default Die in Waffle Pack (400 per tray capacity)
- Sawn Wafer on Tape By specific request
- Unsawn Wafer By specific request
- Die Thickness <> 100µm(4 Mils) On request
- With additional electrical selection On request

### Die Dimensions in µm (mils)





CHIP BACKSIDE IS CATHODE

### **Mechanical Specification**

Die Size (with scribe line)	210 x 210 8.27 x 8.27	µm mils	
Anode Pad Size	130 x 138 5.43 x 5.43	μm mils	
Die Thickness	100 (±15) 3.93 (±0.59)	μm mils	
Top Metal Composition	Al		
Back Metal Composition	AuAs		





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### Absolute Maximum Ratings<sup>1</sup> T<sub>J</sub> = 25°C unless otherwise stated

PARAMETER	SYMBOL	VALUE	UNIT
Repetitive Peak Reverse Voltage	$V_{RRM}$	30	V
DC Blocking Voltage	$V_R$	30	V
DC Forward Current	I <sub>F</sub>	100	mA
Non-repetitive Peak forward surge current <sup>2</sup>	I <sub>FSM</sub>	0.5	А
Power Dissipation	P <sub>D</sub>	400	mW
Operating Junction temperature	TJ	-65 to 150	°C
Storage Temperature Range	T <sub>STG</sub>	-65 to 200	°C

### Electrical Characteristics T<sub>J</sub> = 25°C unless otherwise stated

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNIT
Breakdown Voltage <sup>3</sup>	V <sub>BR</sub>	I <sub>R</sub> = 10μA	30	-	-	V
Forward Voltage <sup>3</sup>		I <sub>F</sub> = 1mA	-	0.33	0.37	V
	V <sub>F</sub>	I <sub>F</sub> = 10mA	-	0.41	0.45	
		I <sub>F</sub> = 35mA	-	0.51	0.55	
Reverse Leakage <sup>3</sup>	I <sub>R</sub>	V <sub>R</sub> = 16V	-	25	200	nA
Junction Capacitance	CJ	$V_R = 0V$ , $f = 1MHz$	-	5.5	-	pF
Reverse Recovery Time	t <sub>rr</sub>	$I_F = I_R = 10 \text{mA},$ $I_{RR} = 0.1 \text{mA}, R_L = 100 \Omega$	-	-	5	ns

<sup>1.</sup> Operation above the absolute maximum rating may cause device failure. Operation at the absolute maximum ratings, for extended periods, may reduce device reliability. 2. 8.3ms single half sine-wave. 3. Pulse test; tp ≤300 μs

### Typical Characteristics T<sub>J</sub> = 25°C unless otherwise stated

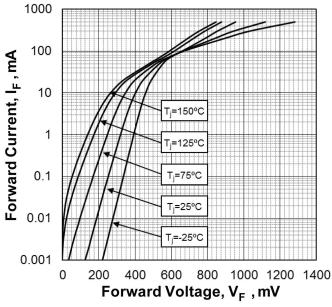


FIGURE 1. Forward Voltage Characteristics

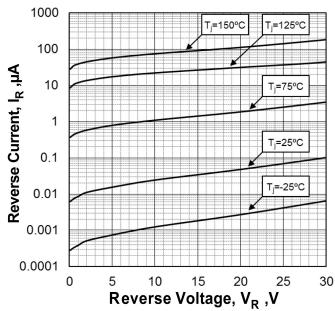


FIGURE 2. Reverse Current Versus Reverse Voltage





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### Typical Characteristics T<sub>J</sub> = 25°C unless otherwise stated

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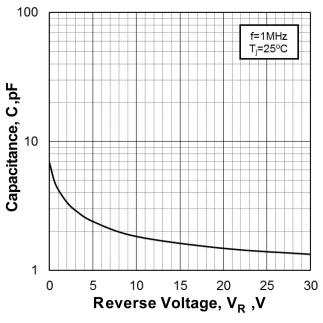


FIGURE 3. Junction Capacitance Versus Reverse Voltage

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